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INFORMATION DISCLOSURE

Application Number 09/760,635

Filing Date 01/16/2001

First Named Inventor Edmond, et al.

Group Art Unit

Examiner Name

Compl te if Known

(use as many sheets as necessary)

Sheet 1 of 4 Attorney Docket Number 5000.137

			U.S. PATENT DOCUM	MENTS	_
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Examiner Initials*	Cite No. ¹	Office ³	Number ⁴	Kind Code ⁵ (<i>if known</i>)	or Applicant of Cited Document	Cited Document MM-DD-YYYY	Where Relevant Passages or Relevant Figures Appear	T ₆
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Complete if Known Application Number 09/760,635 Filing Date 01/16/2001 Edmond, et al. First Named Inventor Group Art Unit **Examiner Name**

Attorney Docket Number Sheet 2 of 4 5000.137 **U.S. PATENT DOCUMENTS** U.S. Patent Document Name of Patentee or Applicant Date of Publication of Pages, Columns, Lines, Where Relevant Cite No.1 Examiner Kind Code² Cited Document Passages or Relevant Figures Appear of Cited Document Number MM-DD-YYYY (if known) 21 6,078,064 Ming-Jiunn et al. 06-20-2000 Duggan 22 6,072,819 06-06-2000 23 6,072,189 05-23-2000 Hashimoto et al. 24 6,067,310 04-04-2000 Schetzina 25 6,046,464 Schetzina 09-23-1997 5,670,798 26 Kimura 02-22-2000 SWU 27 6,028,877 Kimura 02-22-2000

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		OTHER PRIOR ART NON PATENT LITERATURE DOCUMENTS	
		Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	
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Complete if Known **Application Number** 09/760,635 Filing Date 01/16/2001 First Named Inventor Edmond, et al. Group Art Unit **Examiner Name**

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4 Sheet 4 of Attorney Docket Number 5000.137

		OTHER PRIOR ART NON PATENT LITERATURE DOCUMENTS	
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Sheet 1 of 1

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Application Number	09/760635				
Filing Date	January 16, 2001				
First Named Inventor	Edmond et al	-			
Group Art Unit	2811				
Examiner Name					
Attorney Docket Number	5000.137				

				U.S. PATENT DOCUM	MENTS		
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